

Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Sheet 1 of 2

Complete if Known

Application Number	Not Yet Assigned
Filing Date	February 27, 2004
First Named Inventor	Paul A. Farrar
Group Art Unit	unknown
Examiner Name	unknown
Attorney Docket Number	2269-5570.1US (02-1122.01/US)

U.S. PATENT DOCUMENTS

Examiner Initials *	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
<i>JA</i>		US-2,842,438	07/1958	Saarivirta et al.	
<i>JA</i>		US- 5,130,274	07/1992	Harper et al.	
<i>JA</i>		US- 6,077,792	06/2000	Farrar	
<i>JA</i>		US- 6,307,266 B1	10/23/2001	Yung	
<i>JA</i>		US- 6,352,917 B1	3/5/2002	Gupta et al.	
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FOREIGN PATENT DOCUMENTS

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		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)				

Examiner
Signature*Gyane A. Hurley*Date
Considered

7/11/05

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Sheet	2	of	2

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		ANDRICACOS, Panos C., "Copper On-Chip Interconnections", The Electrochemical Society Interface, Spring 1999, pp. 32-39, Vol. 8, No. 1.	
		BRAUD et al., "Ultra Thin Diffusion Barriers for Cu Interconnections at the Gigabit Generation and Beyond", VMIC Conference, June 1996, pp. 174-179, 1996 ISMIC - 106/96/0174(c).	
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		"Improved Metallurgy for Wiring Very Large Scale Integrated Circuits", International Technology Disclosures, 25 Sept. 1986, 1 page, Vol. 4, No. 9.	
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		MARCADAL et al., "OMCVD Copper Process for Dual Damascene Metallization", VMIC Conference, June 1997, pp. 93-98, 1997 ISMIC - 107/97/0093(c).	
		MURARKA et al., "Copper Interconnection Schemes: Elimination of the Need of Diffusion Barriers/Adhesion Promoter by the Use of Corrosion Resistant, Low Resistivity Doped Copper", SPIE, Jan 1994, ppg. 80-90, Vol. 2335.	
		RYU et al., "Barriers for Copper Interconnections", Solid State Technology, April 1999, pp. 1-6, Vol. 42, Issue 4, p53.	
		SAARIVIRTA, Matti J., "High Conductivity Copper-Rich Cu-Zr Alloys", Transactions of the Metallurgical Society of AIME, June 1960, pp. 431-437, Vol. 218, New York, NY.	

Examiner Signature		Date Considered	
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